

Description

The IDT71V321 is a high-speed 2K x 8 Dual-Port Static RAMs with internal interrupt logic for interprocessor communications. The IDT71V321 is designed to be used as a stand-alone 8-bit Dual-Port RAM.

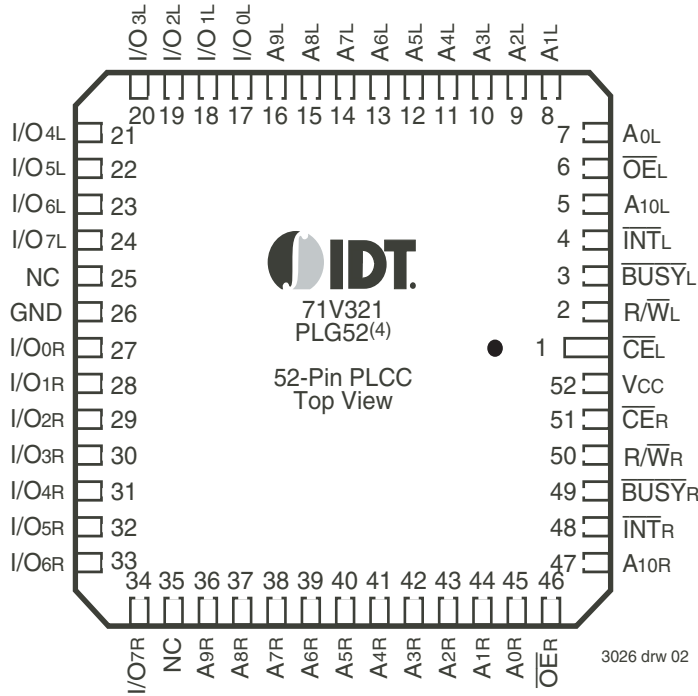
The device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by \overline{CE} , permits the on chip circuitry of each

port to enter a very low standby power mode.

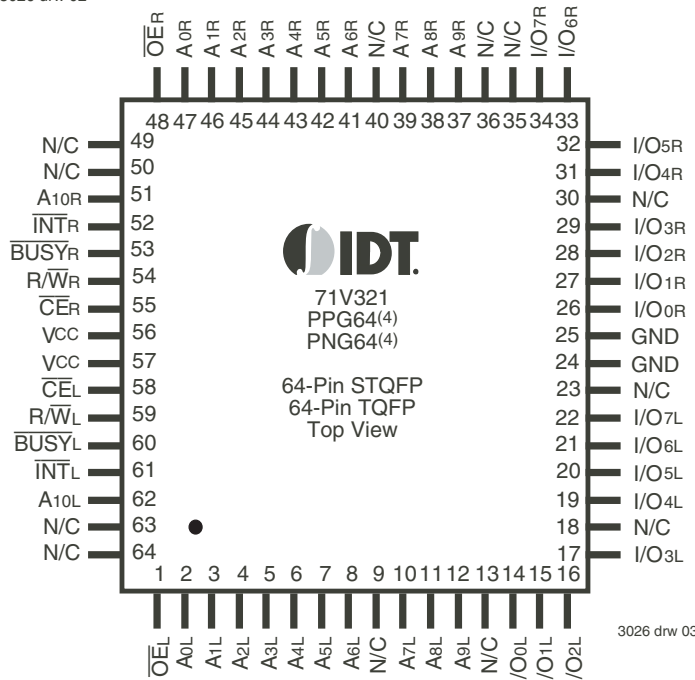
Fabricated using CMOS high-performance technology, these devices typically operate on only 325mW of power. Low-power (L) versions offer battery backup data retention capability, with each Dual-Port typically consuming 200 μ W from a 2V battery.

The IDT71V321 devices are packaged in a 52-pin PLCC, a 64-pin TQFP (thin quad flatpack), and a 64-pin STQFP (super thin quad flatpack).

Pin Configurations^(1,2,3)



3026 drw 02



3026 drw 03

NOTES:

1. All Vcc pins must be connected to power supply.
2. All GND pins must be connected to ground supply.
3. J52-1 package body is approximately .75 in x .75 in x .17 in.
PP64-1 package body is approximately 10mm x 10mm x 1.4mm.
PN64-1 package body is approximately 14mm x 14mm x 1.4mm.
4. This package code is used to reference the package diagram.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
V _{TERM} ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
T _A	Operating Temperature	0 to +70	°C
T _{BIAS}	Temperature Under Bias	-55 to +125	°C
T _{STG}	Storage Temperature	-65 to +150	°C
I _{OUT}	DC Output Current	50	mA

3026 tbl 01

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- V_{TERM} must not exceed V_{CC} + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of V_{TERM} ≥ V_{CC} + 10%.

Capacitance⁽¹⁾

(T_A = +25°C, f = 1.0MHz) TQFP Only

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 3dV	9	pF
C _{OUT}	Output Capacitance	V _{OUT} = 3dV	10	pF

3026 tbl 04

NOTES:

- This parameter is determined by device characterization but is not production tested.
- 3dv references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

Recommended Operating Temperature and Supply Voltage^(1,2)

Grade	Ambient Temperature	GND	V _{CC}
Commercial	0°C to +70°C	0V	3.3V ± 0.3V
Industrial	-40°C to +85°C	0V	3.3V ± 0.3V

3026 tbl 02

NOTES:

- This is the parameter T_A. This is the "instant on" case temperature.
- Industrial temperature: for specific speeds, packages and powers contact your sales office.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Typ.	Max.	Unit
V _{CC}	Supply Voltage	3.0	3.3	3.6	V
GND	Ground	0	0	0	V
V _{IH}	Input High Voltage	2.0	—	V _{CC} +0.3 ⁽²⁾	V
V _{IL}	Input Low Voltage	-0.3 ⁽¹⁾	—	0.8	V

3026 tbl 03

NOTES:

- V_{IL} (min.) = -1.5V for pulse width less than 20ns.
- V_{TERM} must not exceed V_{CC} + 0.3V.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (V_{CC} = 3.3V ± 0.3V)

Symbol	Parameter	Test Conditions	71V321S		71V321L		Unit
			Min.	Max.	Min.	Max.	
I _I	Input Leakage Current ⁽¹⁾	V _{CC} = 3.6V, V _{IN} = 0V to V _{CC}	—	10	—	5	μA
I _O	Output Leakage Current	\overline{CE} = V _{IH} , V _{OUT} = 0V to V _{CC} V _{CC} = 3.6V	—	10	—	5	μA
V _{OL}	Output Low Voltage	I _{OL} = 4mA	—	0.4	—	0.4	V
V _{OH}	Output High Voltage	I _{OH} = -4mA	2.4	—	2.4	—	V

3026 tbl 05

NOTE:

- At V_{CC} ≤ 2.0V input leakages are undefined.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(1,2) (V_{CC} = 3.3V ± 0.3V)

Symbol	Parameter	Test Condition	Version	71V321X25 Com'l & Ind		71V321X35 Com'l & Ind		71V321X55 Com'l & Ind		Unit
				Typ.	Max.	Typ.	Max.	Typ.	Max.	
I _{CC}	Dynamic Operating Current (Both Ports Active)	$\overline{CE} = V_{IL}$, Outputs Disabled $\overline{SEM} = V_{IH}$ $f = f_{MAX}^{(3)}$	COM'L S	55	130	55	125	55	115	mA
			L	55	100	55	95	55	85	
I _{SB1}	Standby Current (Both Ports - TTL Level Inputs)	$\overline{CE}_R = \overline{CE}_L = V_{IH}$ $\overline{SEM}_R = \overline{SEM}_L = V_{IH}$ $f = f_{MAX}^{(3)}$	COM'L S	15	35	15	35	15	35	mA
			L	15	20	15	20	15	20	
I _{SB2}	Standby Current (One Port - TTL Level Inputs)	$\overline{CE}^{*A} = V_{IL}$ and $\overline{CE}^{*B} = V_{IH}^{(5)}$ Active Port Outputs Disabled, $f = f_{MAX}^{(3)}$ $\overline{SEM}_R = \overline{SEM}_L = V_{IH}$	COM'L S	25	75	25	70	25	60	mA
			L	25	55	25	50	25	40	
I _{SB3}	Full Standby Current (Both Ports - All CMOS Level Inputs)	Both Ports \overline{CE}_L and $\overline{CE}_R \geq V_{CC} - 0.2V$ $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} < 0.2V$, $f = 0^{(4)}$ $\overline{SEM}_R = \overline{SEM}_L \geq V_{CC} - 0.2V$	COM'L S	1.0	5	1.0	5	1.0	5	mA
			L	0.2	3	0.2	3	0.2	3	
I _{SB4}	Full Standby Current (One Port - All CMOS Level Inputs)	$\overline{CE}^{*A} < 0.2V$ and $\overline{CE}^{*B} \geq V_{CC} - 0.2V^{(5)}$ $\overline{SEM}_R = \overline{SEM}_L \geq V_{CC} - 0.2V$ $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} < 0.2V$ Active Port Outputs Disabled $f = f_{MAX}^{(3)}$	COM'L S	25	70	25	65	25	55	mA
			L	25	55	25	50	25	40	
			IND L	55	130	55	125	55	115	

3026 tbl 06

NOTES:

- 'X' in part numbers indicates power rating (S or L).
- V_{CC} = 3.3V, T_A = +25°C, and are not production tested. I_{CCDC} = 70mA (Typ.).
- At f = f_{MAX}, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc and using "AC Test Conditions" of input levels of GND to 3V.
- f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby.
- Port "A" may be either left or right port. Port "B" is opposite from port "A".

Data Retention Characteristics (L Version Only)

Symbol	Parameter	Test Condition	Min.	Typ. ⁽¹⁾	Max.	Unit	
V _{DR}	V _{CC} for Data Retention		2.0	—	0	V	
I _{CCDR}	Data Retention Current	V _{CC} = 2V, $\overline{CE} \geq V_{CC} - 0.2V$	COM'L.	—	100	500	μA
t _{CDR} ⁽³⁾	Chip Deselect to Data Retention Time	V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V	IND.	—	100	1000	μA
				0	—	—	V
t _R ⁽³⁾	Operation Recovery Time		t _{RC} ⁽²⁾	—	—	V	

3026 tbl 07

NOTES:

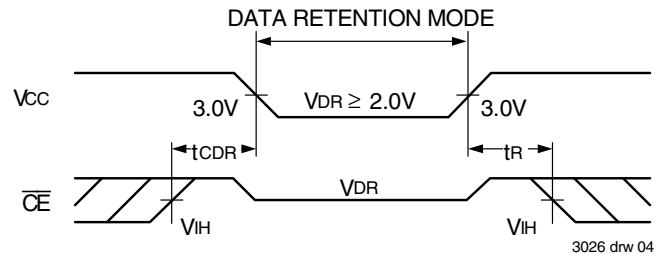
- V_{CC} = 2V, T_A = +25°C, and is not production tested.
- t_{RC} = Read Cycle Time.
- This parameter is guaranteed by device characterization but not production tested.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1 and 2

3026 tbl 08

Data Retention Waveform



3026 drw 04

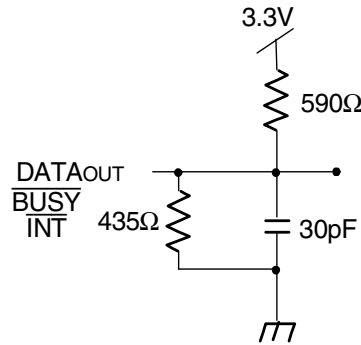
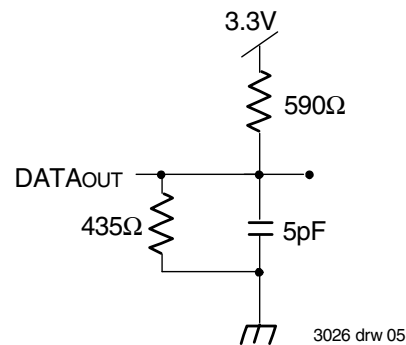


Figure 1. AC Output Test Load



3026 drw 05

Figure 2. Output Test Load
(for tHZ, tLZ, tWZ, and tOW)
* Including scope and jig.

AC Electrical Characteristics Over the Operating Temperature Supply Voltage Range⁽²⁾

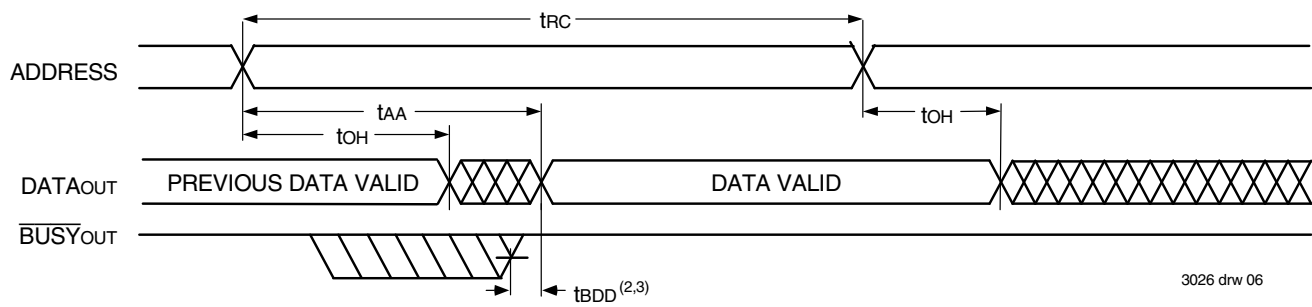
Symbol	Parameter	71V321X25 Com'l & Ind		71V321X35 Com'l & Ind		71V321X55 Com'l & Ind		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE								
tRC	Read Cycle Time	25	—	35	—	55	—	ns
tAA	Address Access Time	—	25	—	35	—	55	ns
tACE	Chip Enable Access Time	—	25	—	35	—	55	ns
tAOE	Output Enable Access Time	—	12	—	20	—	25	ns
tOH	Output Hold from Address Change	3	—	3	—	3	—	ns
tLZ	Output Low-Z Time ^(1,2)	0	—	0	—	0	—	ns
tHZ	Output High-Z Time ^(1,2)	—	12	—	15	—	30	ns
tPU	Chip Enable to Power Up Time ⁽²⁾	0	—	0	—	0	—	ns
tPD	Chip Disable to Power Down Time ⁽²⁾	—	50	—	50	—	50	ns

3026 tbl 09

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).
2. This parameter is guaranteed by device characterization, but is not production tested.
3. 'X' in part numbers indicates power rating (S or L).

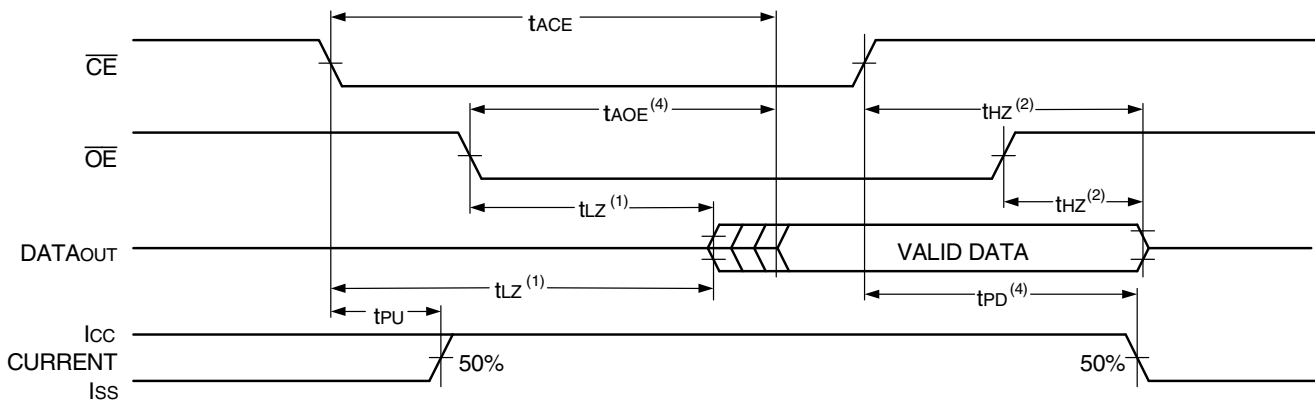
Timing Waveform of Read Cycle No. 1, Either Side⁽¹⁾



NOTES:

1. $R/\bar{W} = V_{IH}$, $\bar{CE} = V_{IL}$, and is $\bar{OE} = V_{IL}$. Address is valid prior to the coincidental with \bar{CE} transition LOW.
2. t_{BDD} delay is required only in the case where the opposite port is completing a write operation to the same address location. For simultaneous read operations $BUSY$ has no relationship to valid output data.
3. Start of valid data depends on which timing becomes effective last t_{AOE} , t_{ACE} , t_{AA} , and t_{BDD} .

Timing Waveform of Read Cycle No. 2, Either Side⁽³⁾



NOTES:

1. Timing depends on which signal is asserted last, \bar{OE} or \bar{CE} .
2. Timing depends on which signal is de-asserted first, \bar{OE} or \bar{CE} .
3. $R/\bar{W} = V_{IH}$ and the address is valid prior to or coincidental with \bar{CE} transition LOW.
4. Start of valid data depends on which timing becomes effective last t_{AOE} , t_{ACE} , t_{AA} , and t_{BDD} .

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁴⁾

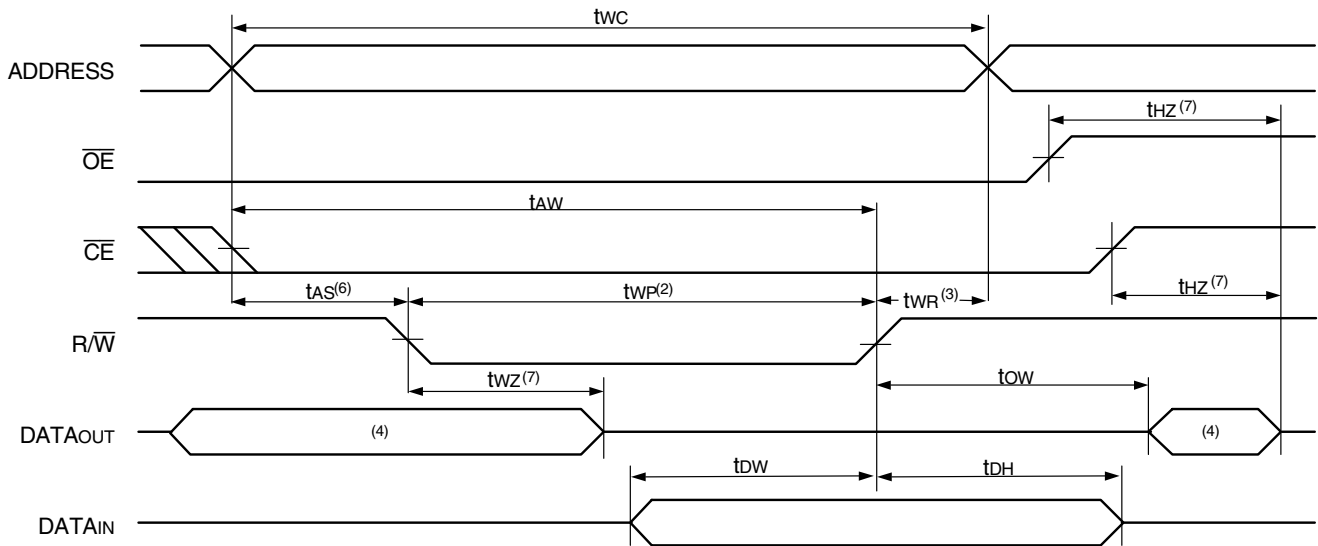
Symbol	Parameter	71V321X25 Com'l & Ind		71V321X35 Com'l & Ind		71V321X55 Com'l & Ind		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
WRITE CYCLE								
t _{wc}	Write Cycle Time	25	—	35	—	55	—	ns
t _{ew}	Chip Enable to End-of-Write	20	—	30	—	40	—	ns
t _{aw}	Address Valid to End-of-Write	20	—	30	—	40	—	ns
t _{as}	Address Set-up Time	0	—	0	—	0	—	ns
t _{wp}	Write Pulse Width	20	—	30	—	40	—	ns
t _{wr}	Write Recovery Time	0	—	0	—	0	—	ns
t _{dw}	Data Valid to End-of-Write	12	—	20	—	20	—	ns
t _{hz}	Output High-Z Time ^(1,2)	—	12	—	15	—	30	ns
t _{dh}	Data Hold Time ⁽³⁾	0	—	0	—	0	—	ns
t _{wz}	Write Enable to Output in High-Z ^(1,2)	—	15	—	15	—	30	ns
t _{ow}	Output Active from End-of-Write ^(1,2)	0	—	0	—	0	—	ns

3026 tbl 10

NOTES:

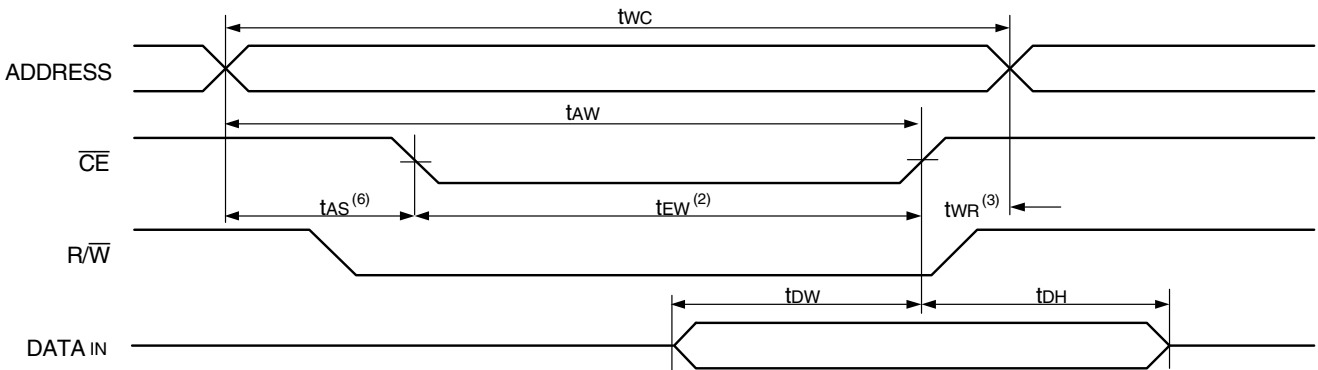
1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).
2. This parameter is guaranteed by device characterization but is not production tested.
3. The specification for t_{dh} must be met by the device supplying write data to the RAM under all operating conditions. Although t_{dh} and t_{ow} values will vary over voltage and temperature, the actual t_{dh} will always be smaller than the actual t_{ow}.
4. 'X' in part numbers indicates power rating (S or L).

Timing Waveform of Write Cycle No. 1, (R/\overline{W} Controlled Timing)^(1,5,8)



3026 drw 08

Timing Waveform of Write Cycle No. 2, (\overline{CE} Controlled Timing)^(1,5)

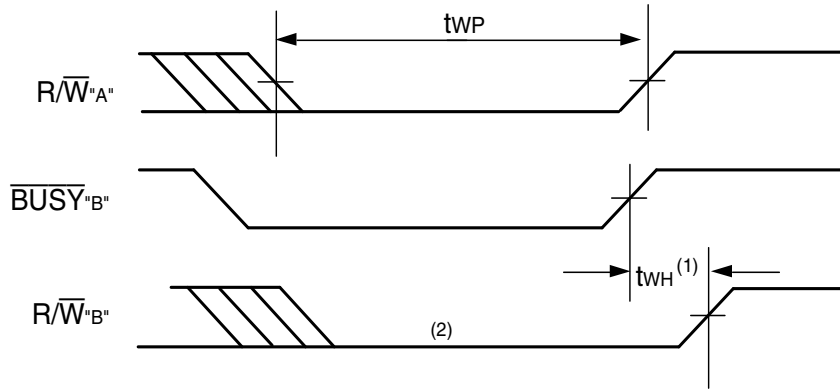


3026 drw 09

NOTES:

1. R/\overline{W} or \overline{CE} must be HIGH during all address transitions.
2. A write occurs during the overlap (t_{EW} or t_{WP}) of $\overline{CE} = V_{IL}$ and $R/\overline{W} = V_{IL}$.
3. t_{WR} is measured from the earlier of \overline{CE} or R/\overline{W} going HIGH to the end of the write cycle.
4. During this period, the I/O pins are in the output state and input signals must not be applied.
5. If the \overline{CE} LOW transition occurs simultaneously with or after the R/\overline{W} LOW transition, the outputs remain in the High-impedance state.
6. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is asserted last.
7. This parameter is determined to be device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
8. If \overline{OE} is LOW during a R/\overline{W} controlled write cycle, the write pulse width must be the larger of t_{WP} or $(t_{WZ} + t_{OW})$ to allow the I/O drivers to turn off data to be placed on the bus for the required t_{OW} . If \overline{OE} is HIGH during a R/\overline{W} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified t_{WP} .

Timing Waveform of Write with **BUSY**⁽³⁾

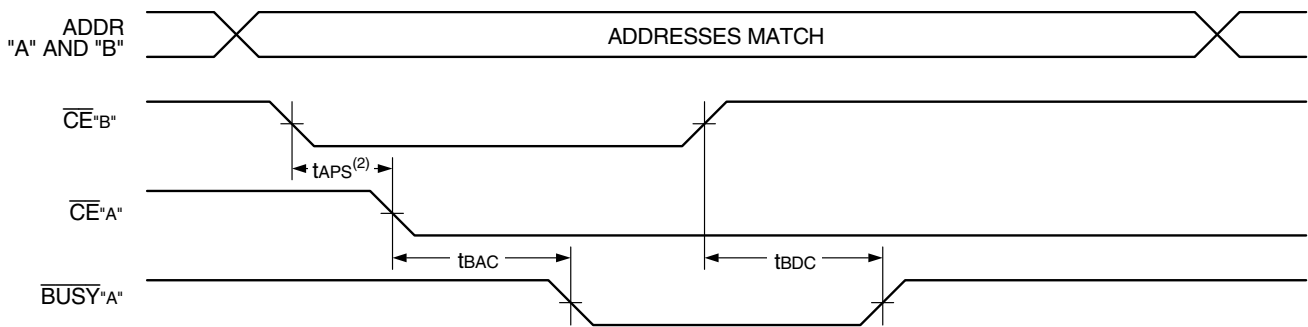


3026 drw 11

NOTES:

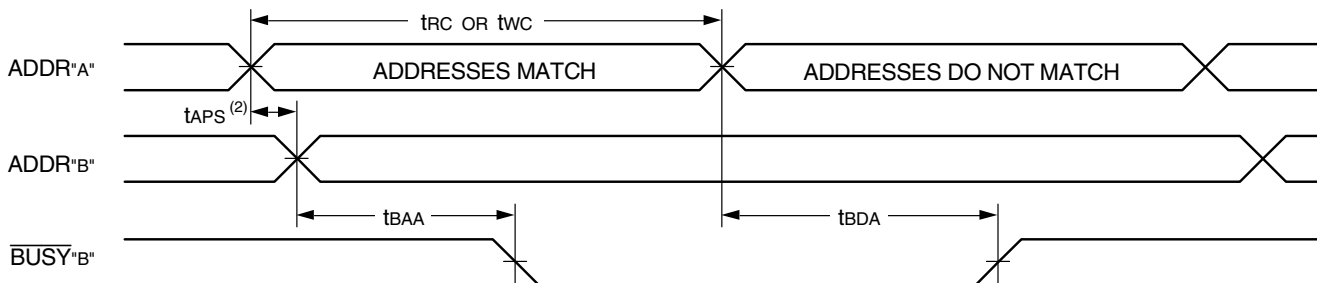
1. t_{WH} must be met for \overline{BUSY} output 71V321.
2. \overline{BUSY} is asserted on port 'B' blocking R/\overline{W} 'B', until \overline{BUSY} 'B' goes HIGH.
3. All timing is the same for the left and right ports. Port "A" may be either the left or right port. Port "B" is opposite from port "A".

Timing Waveform of **BUSY** Arbitration Controlled by \overline{CE} Timing⁽¹⁾



3026 drw 12

Timing Waveform of **BUSY** Arbitration Controlled by Address Match Timing⁽¹⁾



3026 drw 13

NOTES:

1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
2. If t_{APS} is not satisfied, the \overline{BUSY} will be asserted on one side or the other, but there is no guarantee on which side \overline{BUSY} will be asserted.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽¹⁾

Symbol	Parameter	71V321X25 Com'l & Ind		71V321X35 Com'l & Ind		71V321X55 Com'l & Ind		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
INTERRUPT TIMING								
t _{AS}	Address Set-up Time	0	—	0	—	0	—	ns
t _{WR}	Write Recovery Time	0	—	0	—	0	—	ns
t _{INS}	Interrupt Set Time	—	25	—	25	—	45	ns
t _{INR}	Interrupt Reset Time	—	25	—	25	—	45	ns

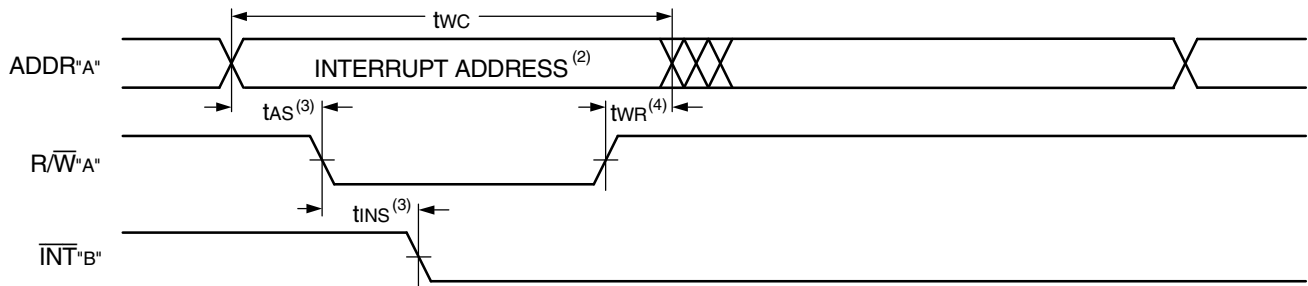
3026 tbl 12

NOTES:

1. 'X' in part numbers indicates power rating (S or L).

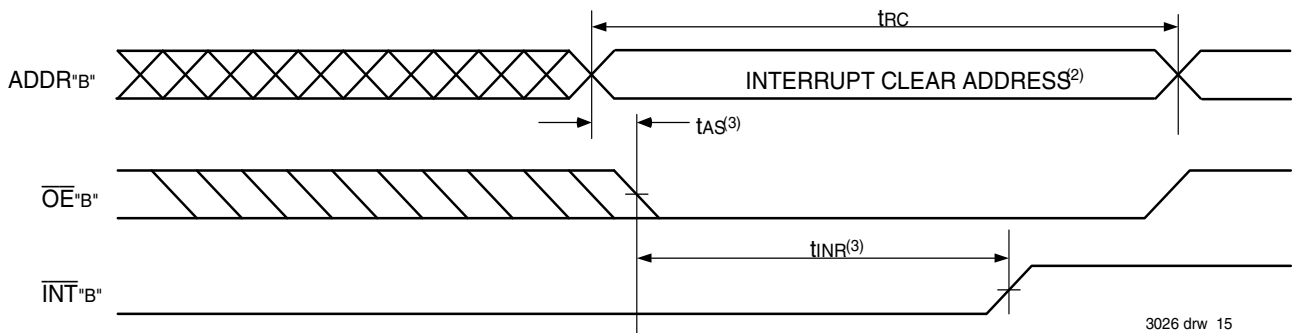
Timing Waveform of Interrupt Mode⁽¹⁾

SET $\overline{\text{INT}}$



3026 drw 14

CLEAR $\overline{\text{INT}}$



3026 drw 15

NOTES:

1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
2. See Interrupt Truth Table.
3. Timing depends on which enable signal ($\overline{\text{CE}}$ or $\overline{\text{R/W}}$) is asserted last.
4. Timing depends on which enable signal ($\overline{\text{CE}}$ or $\overline{\text{R/W}}$) is de-asserted first.

Truth Tables

Table I — Non-Contention Read/Write Control⁽⁴⁾

Left or Right Port ⁽¹⁾				Function
R/W	CE	OE	Do-7	
X	H	X	Z	Port Deselected and in Power-Down Mode. ISB2 or ISB4
X	H	X	Z	$\overline{CE}_R = \overline{CE}_L = V_{IH}$, Power-Down Mode ISB1 or ISB3
L	L	X	DATAIN	Data on Port Written Into Memory ⁽²⁾
H	L	L	DATAOUT	Data in Memory Output on Port ⁽³⁾
H	L	H	Z	High-impedance Outputs

3026 tbl 13

NOTES:

1. A0L – A10L ≠ A0R – A10R.
2. If $\overline{BUSY} = L$, data is not written.
3. If $\overline{BUSY} = L$, data may not be valid, see twDD and tDD timing.
4. 'H' = V_{IH}, 'L' = V_{IL}, 'X' = DON'T CARE, 'Z' = High-impedance.

Table II — Interrupt Flag^(1,4)

Left Port					Right Port					Function
R/WL	CEL	OEL	A10L-A0L	INTL	RWR	CEr	OEr	A10R-A0R	INTR	
L	L	X	7FF	X	X	X	X	X	L ⁽²⁾	Set Right \overline{INTR} Flag
X	X	X	X	X	X	L	L	7FF	H ⁽³⁾	Reset Right \overline{INTR} Flag
X	X	X	X	L ⁽³⁾	L	L	X	7FE	X	Set Left \overline{INTL} Flag
X	L	L	7FE	H ⁽²⁾	X	X	X	X	X	Reset Left \overline{INTL} Flag

3026 tbl 14

NOTES:

1. Assumes $\overline{BUSY}_L = \overline{BUSY}_R = V_{IH}$
2. If $\overline{BUSY}_L = V_{IL}$, then No Change.
3. If $\overline{BUSY}_R = V_{IL}$, then No Change.
4. 'H' = HIGH, 'L' = LOW, 'X' = DON'T CARE

Table III — Address **BUSY** Arbitration

Inputs			Outputs		Function
CEL	CEr	A0L-A10L A0R-A10R	\overline{BUSY}_L ⁽¹⁾	\overline{BUSY}_R ⁽¹⁾	
X	X	NO MATCH	H	H	Normal
H	X	MATCH	H	H	Normal
X	H	MATCH	H	H	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

3026 tbl 15

NOTES:

1. Pins \overline{BUSY}_L and \overline{BUSY}_R are both outputs. \overline{BUSY}_x outputs on the IDT71V321 are totem-pole.
2. 'L' if the inputs to the opposite port were stable prior to the address and enable inputs of this port. 'H' if the inputs to the opposite port became stable after the address and enable inputs of this port. If t_{APS} is not met, either \overline{BUSY}_L or $\overline{BUSY}_R = LOW$ will result. \overline{BUSY}_L and \overline{BUSY}_R outputs cannot be LOW simultaneously.
3. Writes to the left port are internally ignored when \overline{BUSY}_L outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when \overline{BUSY}_R outputs are driving LOW regardless of actual logic level on the pin.

Functional Description

The IDT71V321 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT71V321 has an automatic power down feature controlled by \overline{CE} . The \overline{CE} controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{CE} = V_{IH}$). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag (\overline{INTL}) is asserted when the right port writes to memory location 7FE (HEX), where a write is defined as the $\overline{CE}_R = R/\overline{W}_R = V_{IL}$ per Truth Table II. The left port clears the interrupt by accessing address location 7FE when $\overline{CE}_L = \overline{OE}_L = V_{IL}$, R/W is a "don't care". Likewise, the right port interrupt flag (\overline{INTR}) is asserted when the left port writes to memory location 7FF (HEX) and to clear the interrupt flag (\overline{INTR}), the right port must access the memory location 7FF. The message (8 bits) at 7FE or 7FF is user-defined, since it is an addressable SRAM location. If the interrupt function is not used, address locations 7FE and 7FF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table II for the interrupt operation.

Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The \overline{BUSY} pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a busy indication, the write signal is gated internally to prevent the write from proceeding.

The use of \overline{BUSY} Logic is not required or desirable for all applications. In some cases it may be useful to logically OR the \overline{BUSY} outputs together and use any \overline{BUSY} indication as an interrupt source to flag the event of an illegal or illogical operation.

Depth Expansion

The \overline{BUSY} arbitration, is based on the chip enable and address signals only. It ignores whether an access is a read or write.

The \overline{BUSY} outputs on the IDT71V321 are totem-pole type outputs and do not require pull-up resistors to operate. If these RAMs are being expanded in depth, then the \overline{BUSY} indication for the resulting array requires the use of an external AND gate

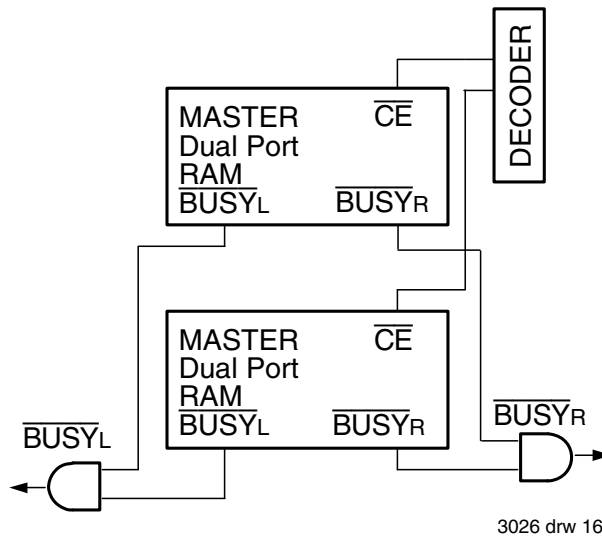
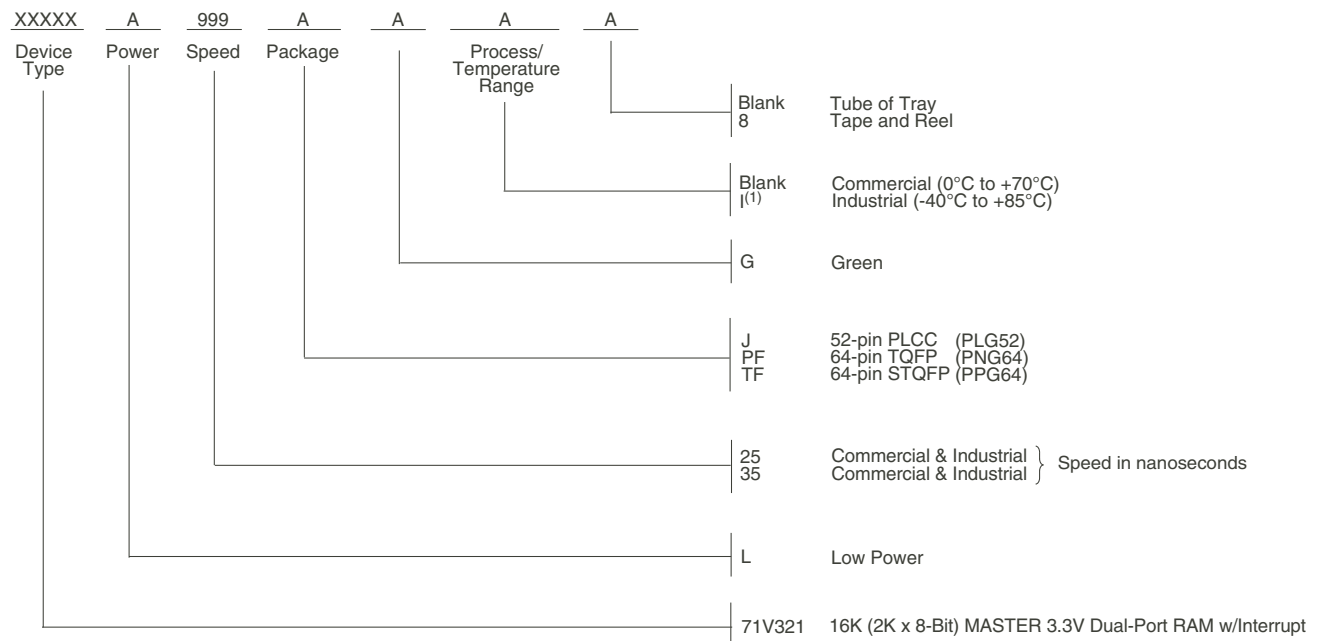


Figure 3. Busy and chip enable routing for depth expansion with IDT71V321.

Ordering Information



3026 drw 17

NOTES:

1. Contact your sales office Industrial temperature range is available for selected speeds, packages and powers.

LEAD FINISH (SnPb) parts are Obsolete. Product Discontinuation Notice - PDN# SP-17-02

Note that information regarding recently obsoleted parts are included in this datasheet for customer convenience.

Orderable Part Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
25	71V321L25JG	PLG52	PLCC	C
	71V321L25JG8	PLG52	PLCC	C
	71V321L25PFG	PNG64	TQFP	C
	71V321L25PFG8	PNG64	TQFP	C
	71V321L25PFGI	PNG64	TQFP	I
	71V321L25PFGI8	PNG64	TQFP	I
	71V321L25TFG	PPG64	TQFP	C
	71V321L25TFG8	PPG64	TQFP	C
	71V321L25TFGI	PPG64	TQFP	I
35	71V321L35JG	PLG52	PLCC	C
	71V321L35JG8	PLG52	PLCC	C
	71V321L35JGI	PLG52	PLCC	I
	71V321L35JGI8	PLG52	PLCC	I
	71V321L35PFGI	PNG64	TQFP	I
	71V321L35PFGI8	PNG64	TQFP	I

Datasheet Document History

03/24/99:	Initiated datasheet document history Converted to new format Cosmetic and typographical corrections Page 2 Added additional notes to pin configurations
06/15/99:	Changed drawing format
10/15/99:	Page 12 Changed open drain to totem-pole in Table III, note 1
10/21/99:	Page 13 Deleted 'does not' in copy from Busy Logic
11/12/99:	Replaced IDT logo
01/12/01:	Page 1 & 2 Moved full "Description" to page 2 and adjusted page layouts Page 3 Increased storage temperature parameters Clarified TA parameter Page 4 DC Electrical parameters—changed wording from "open" to "disabled" Changed $\pm 200\text{mV}$ to 0mV in notes
08/22/01:	Page 4, 5, 7, 9 & 11 Industrial temp range offering removed from DC & AC Electrical Chars for 35 and 55ns
01/17/06:	Page 1 Added green availability to features Page 14 Added green indicator to ordering information Page 1 & 14 Replaced old IDT™ with new IDT™ logo
08/25/06:	Page 11 Changed $\overline{\text{INT}}\text{"A"}$ to $\overline{\text{INT}}\text{"B"}$ in the CLEAR $\overline{\text{INT}}$ drawing in the Timing Waveform of Interrupt Mode
10/23/08:	Page 14 Removed "IDT" from orderable part number
01/25/10:	Page 4 In order to correct the DC Chars table for the 71V321/71V421L35 speed grade and the Data Retention Chars table, I Temp values have been added to each table respectively. In addition, all of the AC Chars tables and the ordering information also now reflect this I temp correction
06/25/15:	Page 2 Removed IDT in reference to fabrication Page 2 & 14 The package codes J52-1, PN64-1 & PP64-1 changed to J52, PN64 & PP64 respectively to match standard package codes Page 14 Added Tape and Reel Indicator to Ordering Information
10/14/15:	Page 1 -15 Removed 71V421S/L from the part number, in the pin configurations and throughout the datasheet Page 1 - 15 Removed all references to Master/Slave throughout the datasheet Page 1 -15 Updated the Com'I and Ind speeds for the 25/35/55ns offerings in Features , in the DC & AC Chars tables, in the Ordering Information and throughout the datasheet Page 13 Removed Width Expansion with Busy Logic Master/Slave Arrays diagram for part numbers 71V321/71V421S/L and updated with a Depth Expansion diagram for the single part number 71V321S/L Updated the corresponding Depth Expansion descriptive text in the Depth Expansion section of the datasheet
01/12/18:	Product Discontinuation Notice - PDN# SP-17-02 Last time buy expires June 15, 2018
07/23/19:	Page 2 Updated package codes J52 to PLG52, PP64 to PPG64 and PN64 to PNG64 Page 14 Added Orderable Part Information table

IMPORTANT NOTICE AND DISCLAIMER

RENESAS ELECTRONICS CORPORATION AND ITS SUBSIDIARIES (“RENESAS”) PROVIDES TECHNICAL SPECIFICATIONS AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES “AS IS” AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS OR IMPLIED, INCLUDING, WITHOUT LIMITATION, ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for developers skilled in the art designing with Renesas products. You are solely responsible for (1) selecting the appropriate products for your application, (2) designing, validating, and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. Renesas grants you permission to use these resources only for development of an application that uses Renesas products. Other reproduction or use of these resources is strictly prohibited. No license is granted to any other Renesas intellectual property or to any third party intellectual property. Renesas disclaims responsibility for, and you will fully indemnify Renesas and its representatives against, any claims, damages, costs, losses, or liabilities arising out of your use of these resources. Renesas' products are provided only subject to Renesas' Terms and Conditions of Sale or other applicable terms agreed to in writing. No use of any Renesas resources expands or otherwise alters any applicable warranties or warranty disclaimers for these products.

(Rev.1.0 Mar 2020)

Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu,
Koto-ku, Tokyo 135-0061, Japan
www.renesas.com

Contact Information

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit:
www.renesas.com/contact/

Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners.